

Abstract

~~Device for treating a surface of a substrate, and a plasma source~~

A device ~~[(1)]~~ for treating a surface of a substrate ~~(9)~~ ~~comprises~~ includes a treatment chamber ~~[(3)]~~ for receiving the substrate therein, and is provided with at least one plasma source ~~[(13)]~~ for generating a plasma ~~[(8)]~~ which is connected to the treatment chamber ~~[(3)]~~. The plasma source ~~[(13)]~~ is provided with an inlet ~~means~~ ~~(11)~~ for admitting at least one reactant into a flow path ~~[(95)]~~ of the plasma ~~[(8)]~~. The plasma source ~~(13)~~ ~~comprises~~ includes at least one cathode ~~[(20)]~~ and at least one anode ~~[(5)]~~ between which a system of cascade plates ~~[(80)]~~ is received. The cascade plates ~~[(80)]~~ are each provided with a number of passage openings ~~[(85)]~~ to provide a number of separate flow paths ~~[(95)]~~ for the plasma ~~[(8)]~~. Situated preceding the first cascade plate ~~[(80)]~~ of the system there is a common plasma space ~~[(90)]~~ which is in open communication with the passage openings ~~[(85)]~~ in the cascade plates ~~[(80)]~~ of the system.

~~[[Fig. 1]]~~